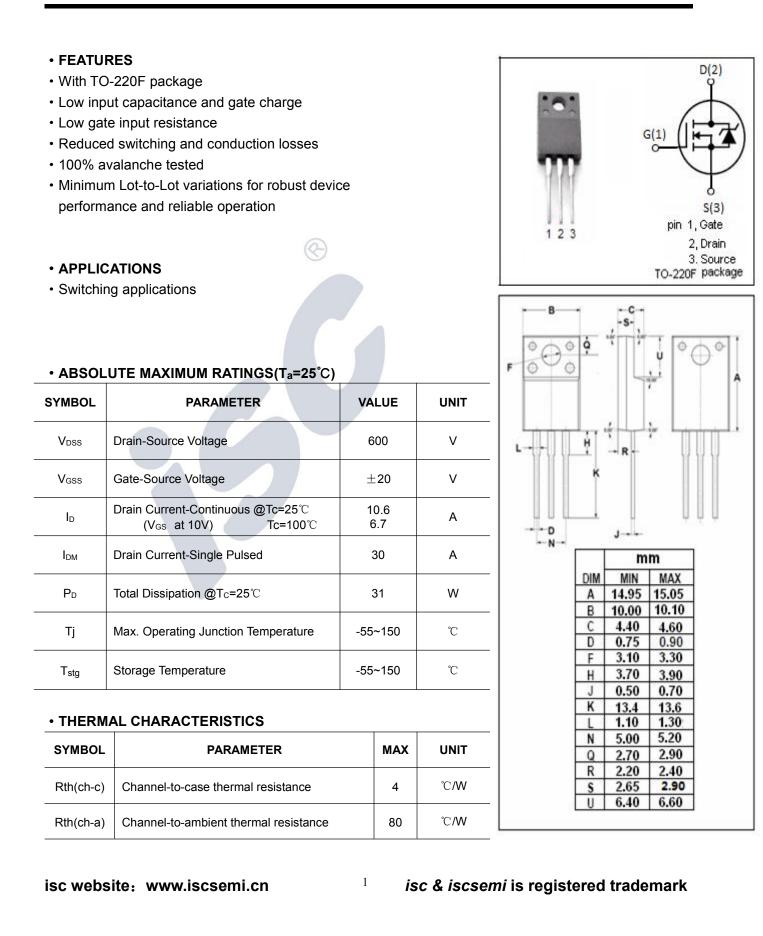


#### INCHANGE SEMICONDUCTOR

## **Isc N-Channel MOSFET Transistor**

## IPA60R380E6





# **Isc N-Channel MOSFET Transistor**

# IPA60R380E6

#### **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> =0.25mA	600			V
V <sub>GS</sub> (th)	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> =0.32mA	2.5	3	3.5	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> =3.8A;Tj=25℃ V <sub>GS</sub> = 10V; I <sub>D</sub> =3.8A; Tj=150℃		0.34 0.89	0.38	Ω
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±20V;V <sub>DS</sub> = 0V			±100	nA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> = 600V; V <sub>GS</sub> = 0V;Tj=25℃ V <sub>DS</sub> = 600V; V <sub>GS</sub> = 0V; Tj=150℃		10	1	μA
V <sub>SDF</sub>	Diode forward voltage	I <sub>SD</sub> =4. 8A, V <sub>GS</sub> = 0 V		0.9		V



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